

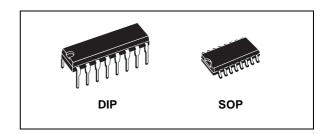


BCD TO SEVEN SEGMENT LATCH/DECODER/DRIVER

- HIGH OUTPUT SOURCING CAPABILITY (up to 25mA).
- INPUT LATCHES FOR BCD CODE STORAGE
- LAMP TEST AND BLANKING CAPABILITY.
- 7-SEGMENT OUTPUTS BLANKED FOR BCD INPUT CODES > 1001
- QUIESCENT CURRENT SPECIF. UP TO 20V
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

HCF4511B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. HCF4511B is a BCD to 7 segment decoder driver made up of CMOS logic and n-p-n bipolar transistor output devices on a single monolithic structure. This device combines the low quiescent



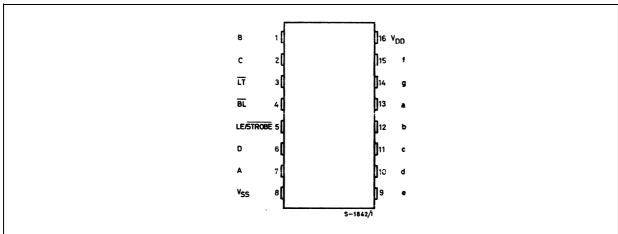
ORDER CODES

PACKAGE	TUBE	T&R
DIP	HCF4511BEY	
SOP	HCF4511BM1	HCF4511M013TR

power dissipation and high noise immunity features of CMOS with n-p-n bipolar output transistor capable of sourcing up to 25mA. This capability allows HCF4511B to drive LEDs and other displays directly.

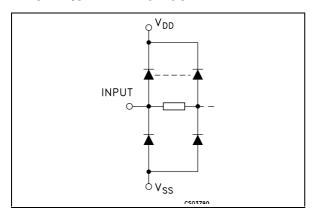
Lamp Test (LT), Blanking (BL), and Latch Enable or Strobe inputs are provided to test the display, shut off or intensity-modulate it, and store or strobe a BCD code, respectively. Several different signals may be multiplexed and displayed when external multiplexing circuitry is used.

PIN CONNECTION



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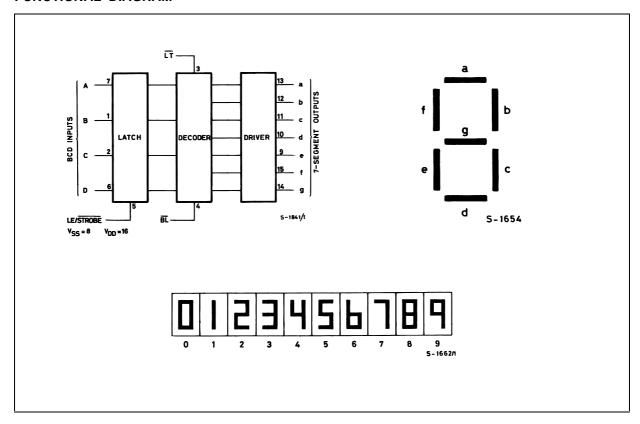
INPUT EQUIVALENT CIRCUIT



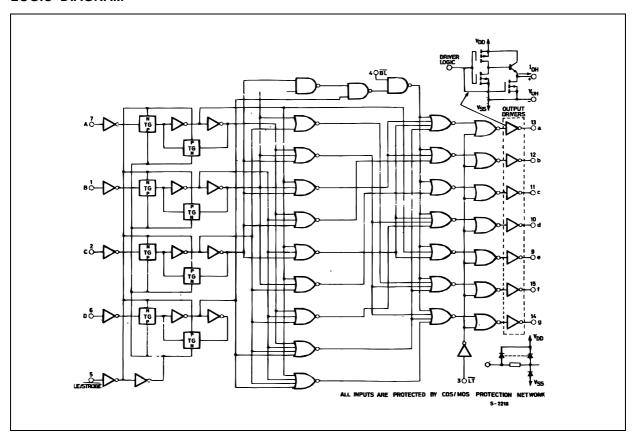
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
7, 1, 2, 6	A, B, C, D	Bcd Inputs
13, 12, 11, 10, 9, 15, 14	a to g	7-Segment Outputs
3	LT	Lamp Test Input
4	BL	Blanking Input
5	LE/STROBE	Latch Enable or Strobe Input
8	V_{SS}	Negative Supply Voltage
16	V_{DD}	Positive Supply Voltage

FUNCTIONAL DIAGRAM



LOGIC DIAGRAM



TRUTH TABLE

LE	BL	ΙΤ	D	С	В	Α	а	b	С	d	е	f	g	DISPLAY
Х	Х	L	Χ	Χ	Χ	Х	Н	Н	Н	Н	Н	Н	Н	8
Х	L	Н	X	X	Х	Х	L	L	L	L	L	L	L	Blank
L	Н	Н	L	L	L	L	Н	Н	Н	Н	Н	Н	L	0
L	Н	Н	L	L	L	Н	L	Н	Н	L	L	L	L	1
L	Н	Н	L	L	Н	L	Н	Н	L	Н	Н	L	Н	2
L	Н	Н	L	L	Н	Н	Н	Н	Н	Н	L	L	Н	3
L	Н	Н	L	Н	L	L	L	Н	Н	L	L	Н	Н	4
L	Н	Н	L	Н	L	Н	Н	L	Н	Н	L	Н	Н	5
L	Н	Н	L	Н	Н	L	L	L	Н	Н	Н	Н	Н	6
L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	L	L	L	7
L	Н	Н	Н	L	L	L	Н	Н	Н	Н	Н	Н	Н	8
L	Н	Н	Н	L	L	Н	Н	Н	Н	L	L	Н	Н	9
L	Н	Н	Н	L	Н	L	L	L	L	L	L	L	L	Blank
L	Н	Н	Н	L	Н	Н	L	L	L	L	L	L	L	Blank
L	Н	Н	Н	Н	L	L	L	L	L	L	L	L	L	Blank
L	Н	Н	Н	Н	L	Н	L	L	L	L	L	L	L	Blank
L	Н	Н	Н	Н	Н	L	L	L	L	L	L	L	L	Blank
L	Н	Н	Н	Н	Н	Н	L	L	L	L	L	L	L	Blank
Н	Н	Н	Χ	Χ	Χ	Χ				*				*

X: Don't Care

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	-0.5 to +22	V
V _I	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
I	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	٧
V _I	Input Voltage	0 to V _{DD}	٧
T _{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

			Test Con	dition		Value							
Symbol	Parameter	VI	v _o	I _O	V_{DD}	Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)	(V)	(μA)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Current	0/5			5		0.04	5		150		150	
		0/10			10		0.04	10		300		300	μΑ
		0/15			15		0.04	20		600		600	μΛ
		0/20			20		0.08	100		3000		3000	
V_{OH}	High Level Output	0/5			5	4.95			4.95		4.95		
	Voltage	0/10			10	9.95			9.95		9.95		V
		0/15			15	14.95			14.95		14.95		
V _{OL}	Low Level Output	5/0			5		0.05			0.05		0.05	
	Voltage	10/0			10		0.05			0.05		0.05	V
		15/0			15		0.05			0.05		0.05	
V _{IH}	High Level Input		0.5/3.8		5	3.5			3.5		3.5		
	Voltage		1/8.8		10	7			7		7		V
			1.5/13.8		15	11			11		11		
V _{IL}	Low Level Input		3.8/0.5		5			1.5		1.5		1.5	
"-	Voltage		8.8/1		10			3		3		3	V
			13.8/1.5 15 0 4.1		4		4		4				
V _{OH}	Output Drive		1010,110	0		4.1	4.57	-	4.1		4.1		
- ОП	Voltage			5			4.24						V
				10		3.6	4.12		3.3		3.3		
				15	5	0.0	3.94		0.0		0.0		
				20		2.8	3.75		2.5		2.5	v	
				25		2.0	3.54		2.0		2.0		
				0		9.1	9.58		9.1		9.1		
				5		5.1	9.26		5.1		5.1		
				10		8.75	9.17		8.45		8.45		
				15	10	0.73	9.04		0.43		0.43		V
				20		8.1	8.90		7.8		7.8		
				25		0.1	8.75		7.0		7.0		
				0		14.1	14.59		14.1		14.1		
				5		14.1	14.39		14.1		14.1		
				10		13.75	14.18		13.45		13.45		
					15	13.75	14.10		13.45		13.45		V
				15 20		13.1			12.8		12.8		
				25		13.1	13.95 13.80		12.8		12.δ		
	Output Sink	0/5	0.4	∠5	5	0.44	13.80		0.36		0.00		
I _{OL}	Current		0.4								0.36		mA
	3.1011	0/10	0.5		10	1.1	2.6		0.9		0.9		mA
	lament lambara	0/15	1.5		15	3	6.8		2.4		2.4		
I _I	Input Leakage Current (any input)	0/18			18		±10 ⁻⁵	±0.1		±1		±1	μΑ
CI	Input Capacitance (any input)						5	7.5					pF

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} =5V, 2V min. with V_{DD} =10V, 2.5V min. with V_{DD} =15V

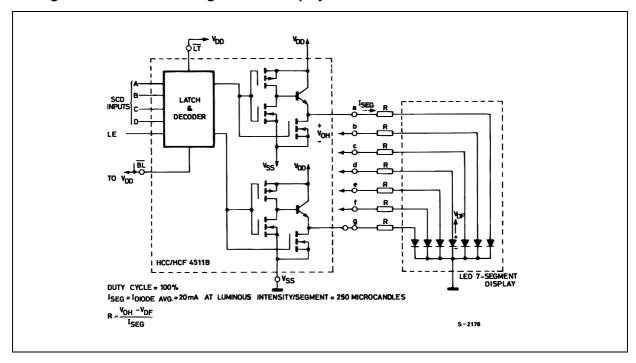
$\textbf{DYNAMIC ELECTRICAL CHARACTERISTICS} \ (\textbf{T}_{amb} = 25^{\circ} \textbf{C}, \ \textbf{C}_{L} = 50 \text{pF}, \ \textbf{R}_{L} = 200 \text{K}\Omega, \ \textbf{t}_{r} = \textbf{t}_{f} = 20 \text{ ns})$

			TEST CONDITION	,	Value (*) Unit Min. Typ. Max. Image: Colspan="2">Max. 520 1040		
Symbol	Parameter	V _{DD} (V)		Min.	Тур.	Max.	
t _{PHL}	Propagation Delay Time	5			520	1040	
	(DATA)	10			210	420	ns
		15			150	300	
t _{PLH}	Propagation Delay Time	5			660	1320	
	(DATA)	10			260	520	ns
		15			180	360	
t _{PHL}	Propagation Delay Time	5			350	700	
	(BL)	10			175	350	ns
		15			125	250	
t _{PLH}	Propagation Delay Time	5			400	800	
	(BL)	10			175	350	ns
		15			150	300	
t _{PHL}	Propagation Delay Time	5			250	500	
	(LT)	10			125	250	ns
		15			85	170	
t _{PLH}	Propagation Delay Time	5			150	300	
	(LT)	10			75	150	ns
		15			50	100	
t _{TLH}	Transition Time	5			40	80	
		10			30	60	ns
		15			20	50	
t _{THL}	Transition Time	5			125	310	
		10			75	185	ns
		15			65	160	1
t _{setup}	Setup Time	5		150	75		
оогар		10		70	35		ns
		15		40	20		
t _{hold}	Hold Time	5		0	-75		
		10		0	-35		ns
		15		0	-20		
t _W	Strobe Pulse Width	5		400	200		
		10		160	80		ns
		15		100	50		

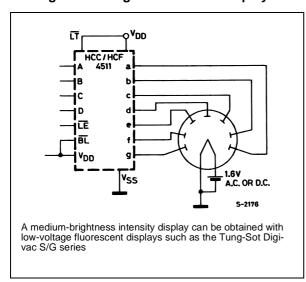
^(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.

TYPICAL APPLICATIONS (Interfacing with various displays)

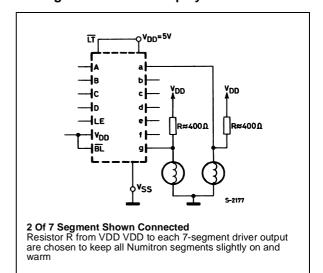
Driving Common-cathode 7 Segment Led Displays



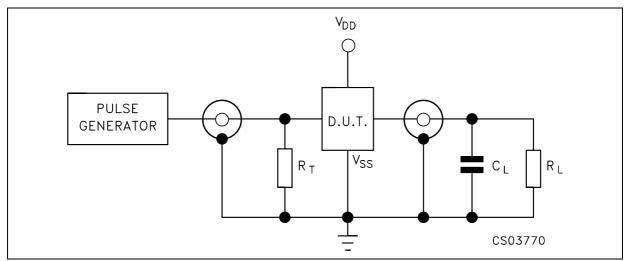
Driving Low-voltage Fluorescent Displays



Driving Incandescent Displays

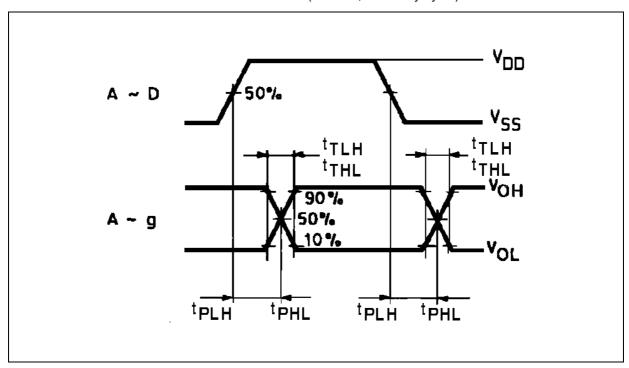


TEST CIRCUIT



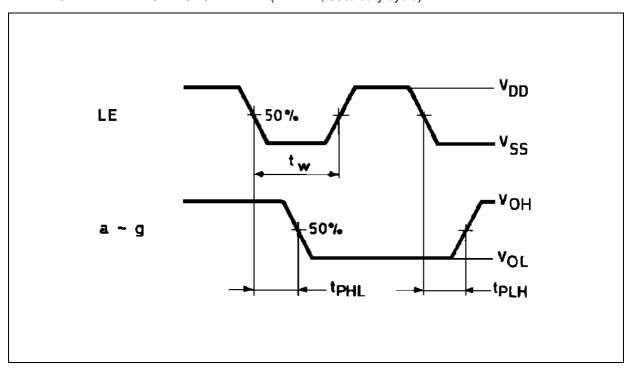
 C_L = 50pF or equivalent (includes jig and probe capacitance) R_L = 200K Ω R_T = Z_{OUT} of pulse generator (typically 50 Ω)

WAVEFORM 1: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)

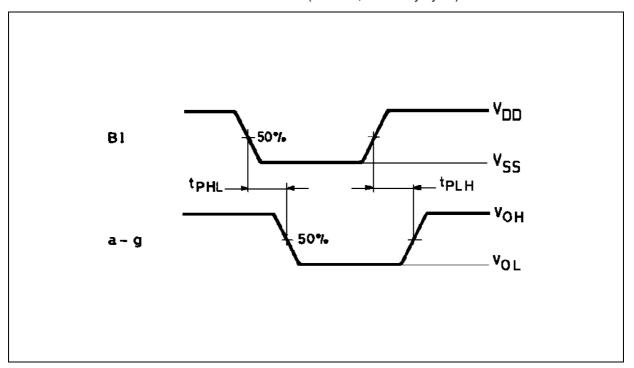


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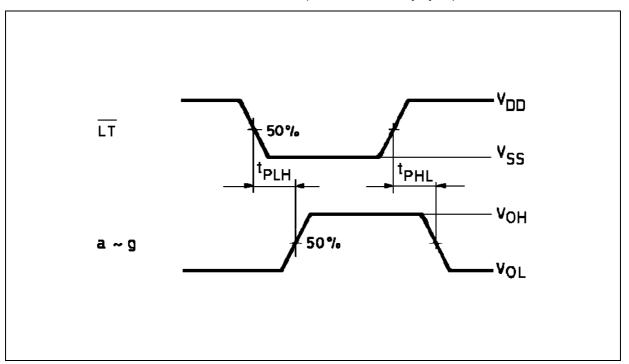
WAVEFORM 2: MINIMUM PULSE WIDTH (f=1MHz; 50% duty cycle)



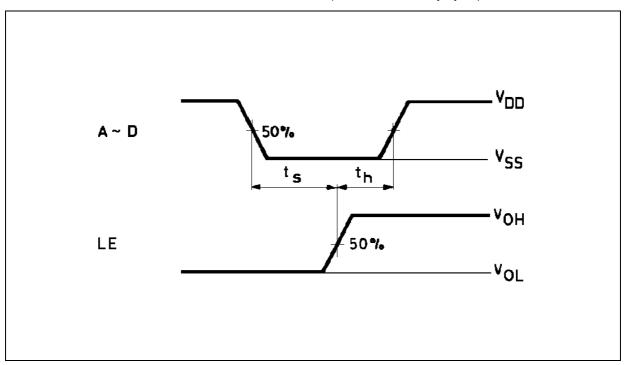
WAVEFORM 3: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



WAVEFORM 4: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)

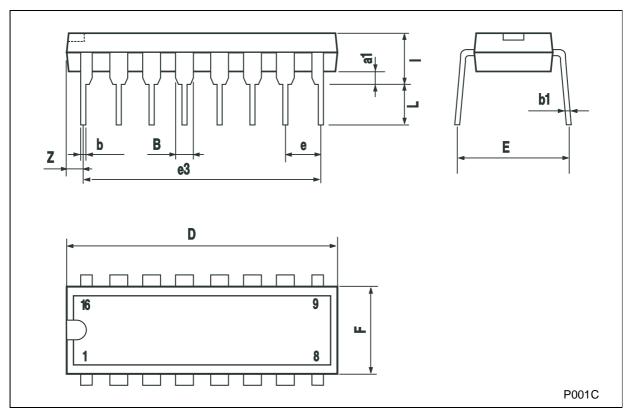


WAVEFORM 5: MINIMUM SETUP AND HOLD TIME (f=1MHz; 50% duty cycle)



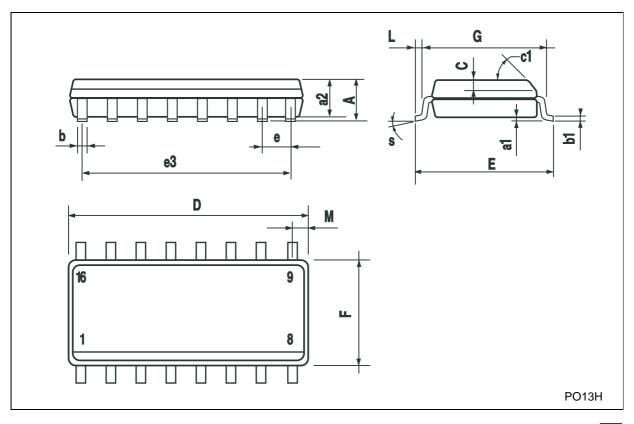
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM.		mm.		inch					
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.			
a1	0.51			0.020					
В	0.77		1.65	0.030		0.065			
b		0.5			0.020				
b1		0.25			0.010				
D			20			0.787			
E		8.5			0.335				
е		2.54			0.100				
e3		17.78			0.700				
F			7.1			0.280			
I			5.1			0.201			
L		3.3			0.130				
Z			1.27			0.050			



SO-16 MECHANICAL DATA

DIM.		mm.		inch					
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.			
Α			1.75			0.068			
a1	0.1		0.2	0.003		0.007			
a2			1.65			0.064			
b	0.35		0.46	0.013		0.018			
b1	0.19		0.25	0.007		0.010			
С		0.5			0.019				
c1			45°	(typ.)	•				
D	9.8		10	0.385		0.393			
E	5.8		6.2	0.228		0.244			
е		1.27			0.050				
e3		8.89			0.350				
F	3.8		4.0	0.149		0.157			
G	4.6		5.3	0.181		0.208			
L	0.5		1.27	0.019		0.050			
М			0.62			0.024			
S		•	8° (ı	max.)	•	1			



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